



SIDC56D60E6

Fast switching diode chip in EMCON-Technology

FEATURES:

- 600V EMCON technology 70 µm chip
- · soft , fast switching
- low reverse recovery charge
- small temperature coefficient

This chip is used for:

EUPEC power modules and discrete devices



Applications:

SMPS, resonant applications, drives

Chip Type	V_R	I _F	Die Size	Package	Ordering Code
SIDC56D60E6	600V	150A	7.5 x 7.5 mm ²	sawn on foil	C67047-A4687-
3.2 332 3020	000 v	100/	7.5 x 7.5 mm	Sawii dii idii	A001

MECHANICAL PARAMETER:

MEGHANIGAE I ANAMETEN:					
Raster size	7.5 x 7.5				
Area total / active	56.25 / 46.65	mm ²			
Anode pad size	6.78 x 6.78				
Thickness	70	μm			
Wafer size	150	mm			
Flat position	180	deg			
Max. possible chips per wafer	248 pcs				
Passivation frontside	Photoimide				
Anode metallisation	3200 nm AlSiCu				
Cathode metallisation	1400 nm Ni Ag –system suitable for epoxy and soft solder die bonding				
Die bond	electrically conductive glue or solder				
Wire bond	AI, ≤500μm				
Reject Ink Dot Size	Ø 0.65mm; max 1.2mm				
Recommended Storage Environment	store in original container, in dry nitrogen, < 6 month at an ambient temperature of 23°C				



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Maximum Ratings

Parameter	Symbol	Condition	Value	Unit
Repetitive peak reverse voltage	V_{RRM}		600	V
Continuous forward current limited by T_{jmax}	I _F		150	
Single pulse forward current (depending on wire bond configuration)	I _{FSM}	$t_P = 10 \text{ ms sinusoidal}$	tbd	Α
Maximum repetitive forward current limited by T_{jmax}	I _{FRM}		450	
Operating junction and storage temperature	$T_{\rm j}$, $T_{ m stg}$		-55+150	°C

Static Electrical Characteristics (tested on chip), T_i =25 °C, unless otherwise specified

Parameter	Symbol	Condi	Value			Unit	
raidilletei	Syllibol	Cond	min.	Тур.	max.		
Reverse leakage current	I_{R}	V _R =600V	<i>T_j</i> =25 °C			27	μΑ
Cathode-Anode breakdown Voltage	V_{Br}	I _R =4mA	<i>T_j</i> =25°C	600			V
Forward voltage drop	V_F	I _F =150A	<i>T_j</i> =25°C		1.25		V

Dynamic Electrical Characteristics, at $T_j = 25$ °C, unless otherwise specified, tested at component

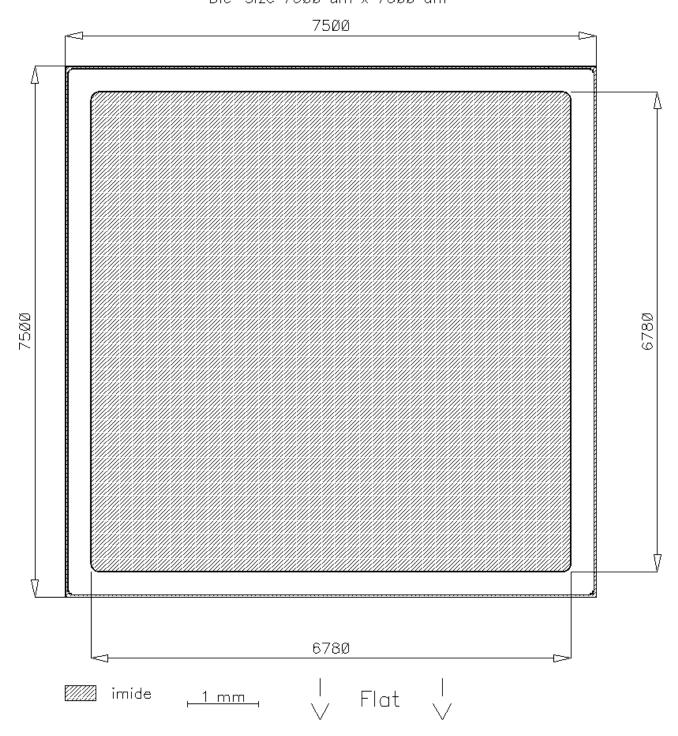
Parameter	Symbol	Conditions		Value			Unit
raiailletei	Syllibol			min.	Тур.	max.	
Reverse recovery time	t _{rr1}	$I_F=150A$	$T_j = 25$ °C		tbd		
	t _{rr2}	$di/dt=5600A/ms$ $V_R=300V$	$T_j = 125$ °C				ns
Peak recovery current	I _{RRM1}	I _F =150A	$T_j = 25$ °C		190.2		Α
	I _{RRM2}	$\begin{array}{c} di/dt = 5600 A/ms \\ V_R = 300 V \end{array}$	$T_j = 125$ °C		228.5]^
Reverse recovery charge	Q _{rr1}	$I_F = 150A$	<i>T_j</i> =25°C		9.97		μC
	Q _{rr2}	$\frac{\text{di/dt=5600A/ms}}{V_{R}=300V}$	T _j =125°C		16.5		
Peak rate of fall of reverse	di _{rr1} /dt	I _F =150A	T _j =25°C		tbd		A / -
recovery current	di _{rr2} /dt	$di/dt=5600A/ms$ $V_R=300V$	T _j =125°C				A/μs
Softness	S1	$I_F = 150A$ di/dt=5600A/ms	<i>T_j</i> =25 °C		tbd		1
	S2	$V_R = 300 V$	T _j =125°C				<u> </u>



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CHIP DRAWING:

L422B1 Die-Size 7500 um x 7500 um



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Preliminary

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FURTHER ELECTRICAL CHARACTERISTICS:

This chip data sheet refers to the device data sheet	INFINEON TECHNOLOGIES / EUPEC	tbd	

Description:

AQL 0,65 for visual inspection according to failure catalog

Electrostatic Discharge Sensitive Device according to MIL-STD 883

Test-Normen Villach/Prüffeld

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